

# Introduction of X-ray (XPS, XES, and XAS) analysis method

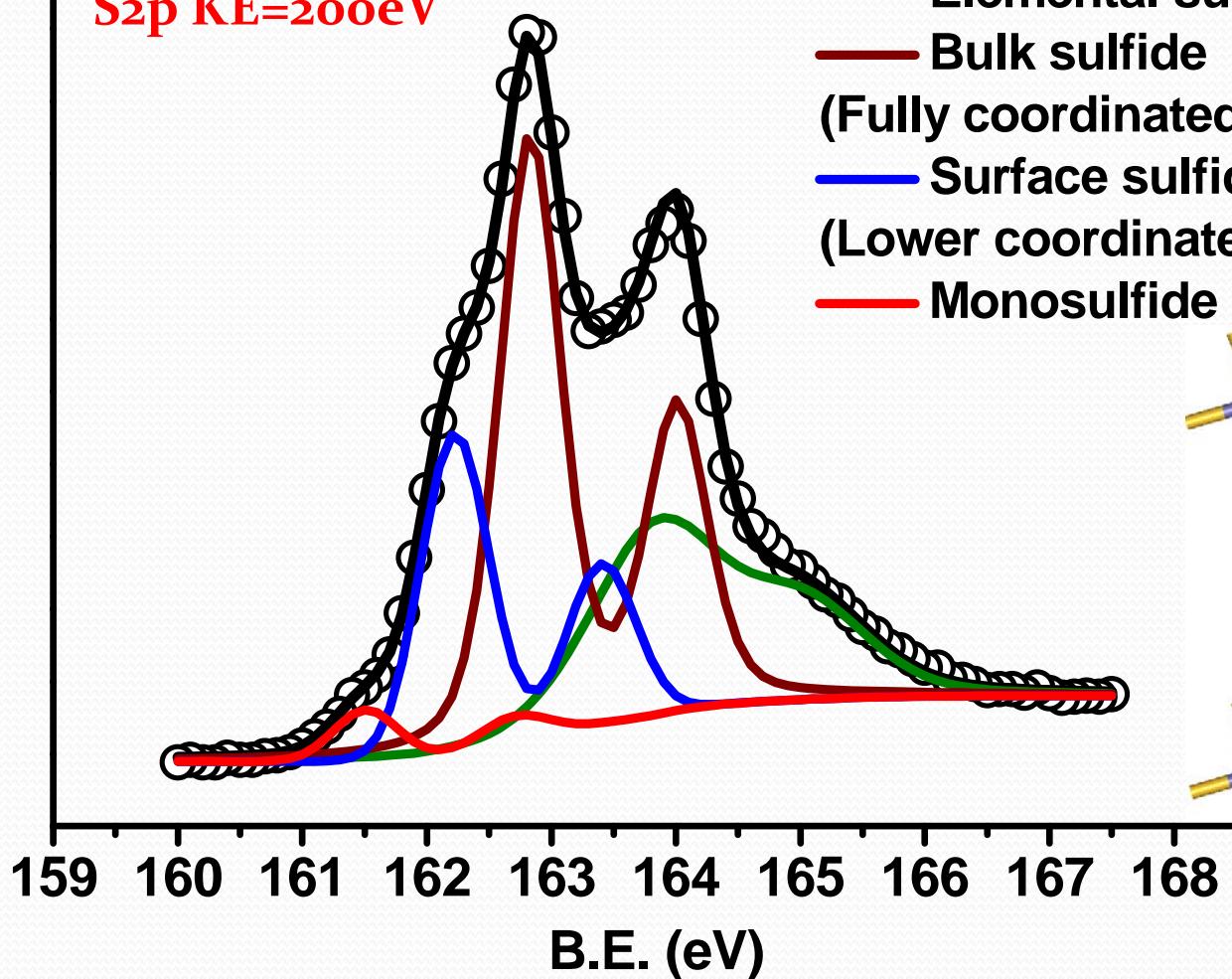
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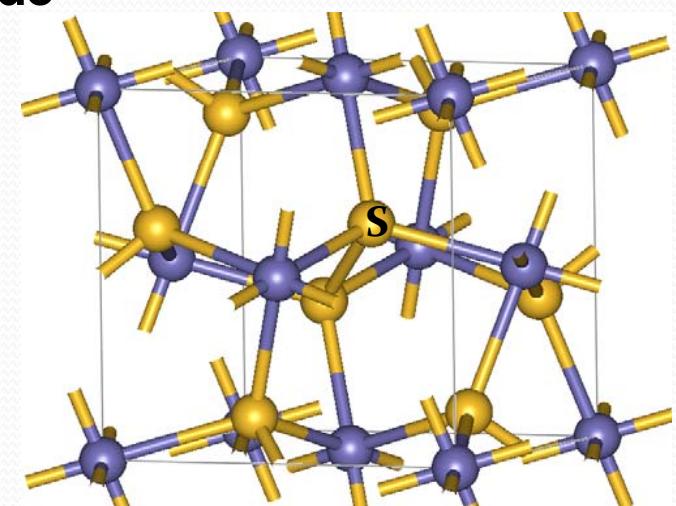
January 11, 2011

# Surface structure of Pyrite thin films on Si

S<sub>2</sub>p KE=200eV



- Raw
- Fitting
- Elemental sulfur
- Bulk sulfide
- (Fully coordinated, 1S, 3Fe)
- Surface sulfide
- (Lower coordinated 1S, 2Fe)
- Monosulfide



# **Advanced X-Ray Analysis Methods**

**XPS (Photoemission) → Binding Energy  
(beamline 11.0.2, beamline 9.3.2)**

**XAS (Absorption) → Unoccupied Density of state (HOMO)  
(beamline 11.0.1, beamline 10.3.2)**

**XES (Emission) → Occupied Density of state (LOMO)  
(beamline 8.0.1)**



All in one?

XPS, XAS, XES all in Beamline 11.0.2?

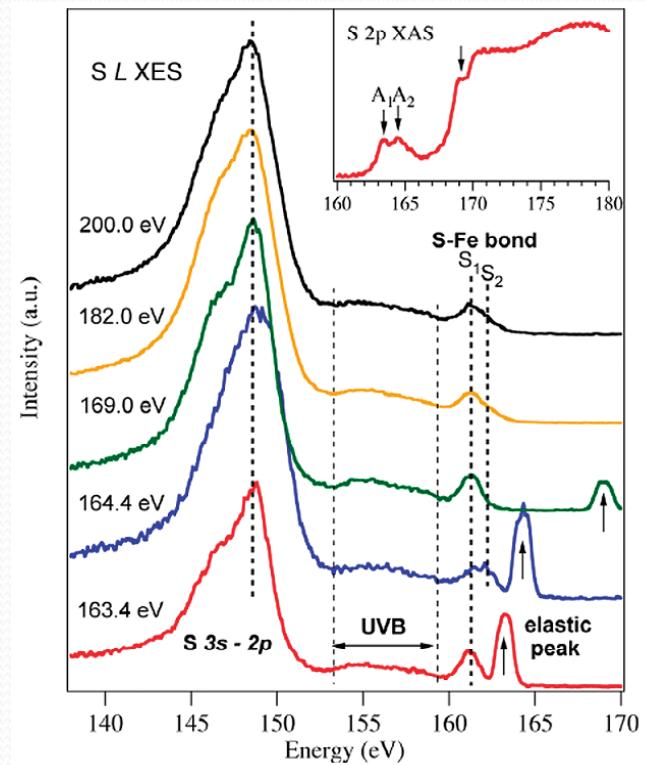
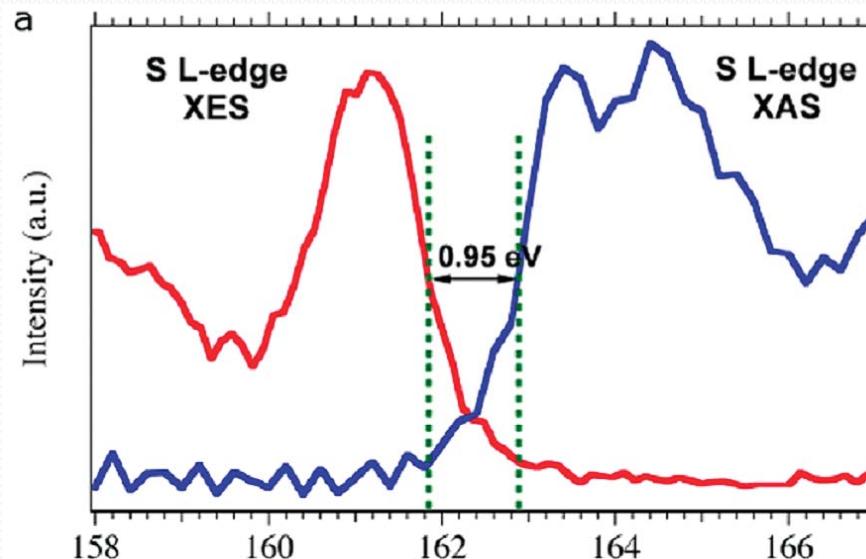
# Purpose

- XPS & Electron Yield XAS

- Binding Energy, Density of State of Conduction Band
- Fermi Surface Determination: Valence Band Spectrum, or know BE element
- Band Gap
- Testing experiment on Si

- Electron Yield XES & XAS

- Density of State of Valence and Conduction Band
- Band Gap and Core Hole Effect

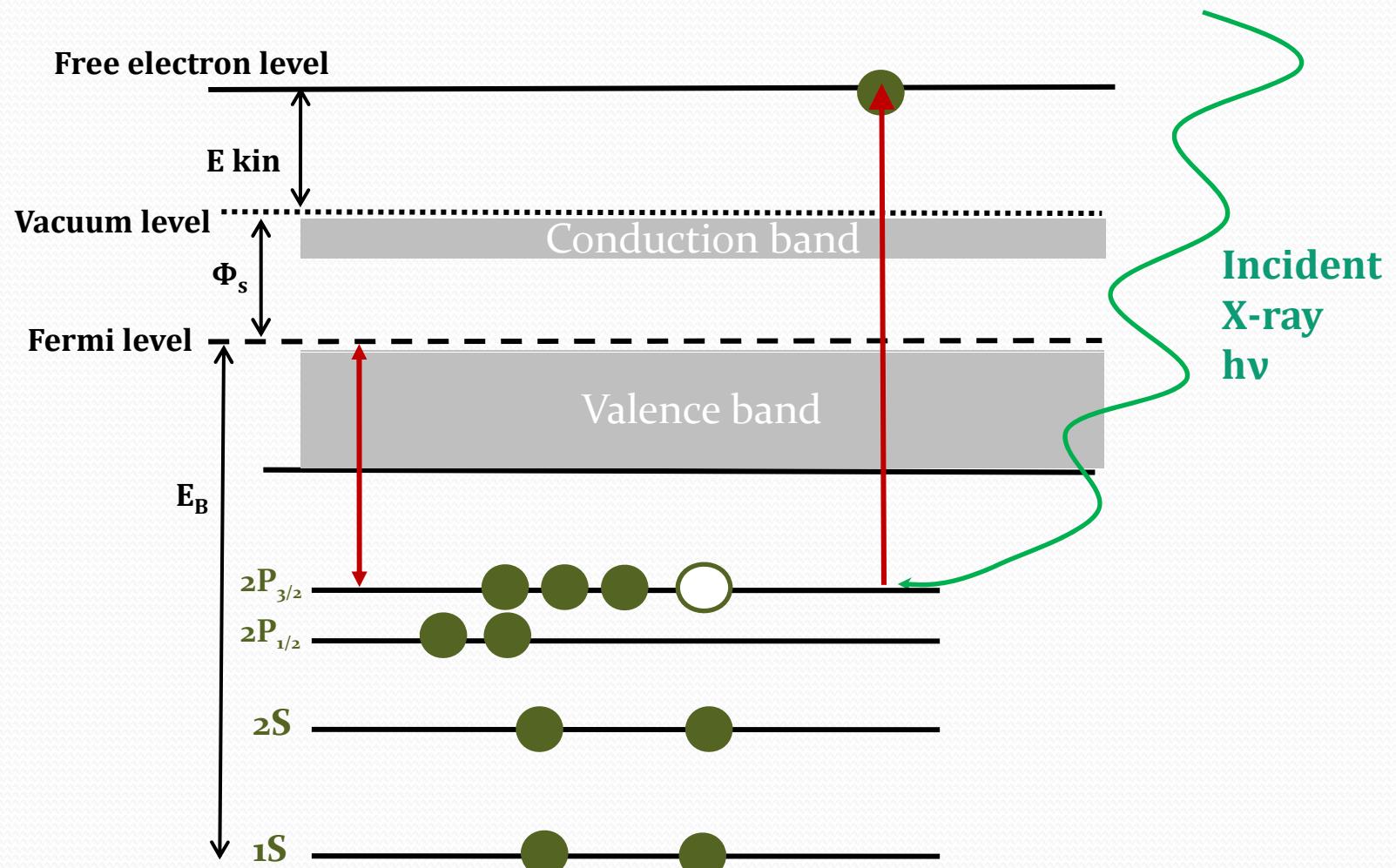




# XPS

## One Photon process: Photon in Electron out

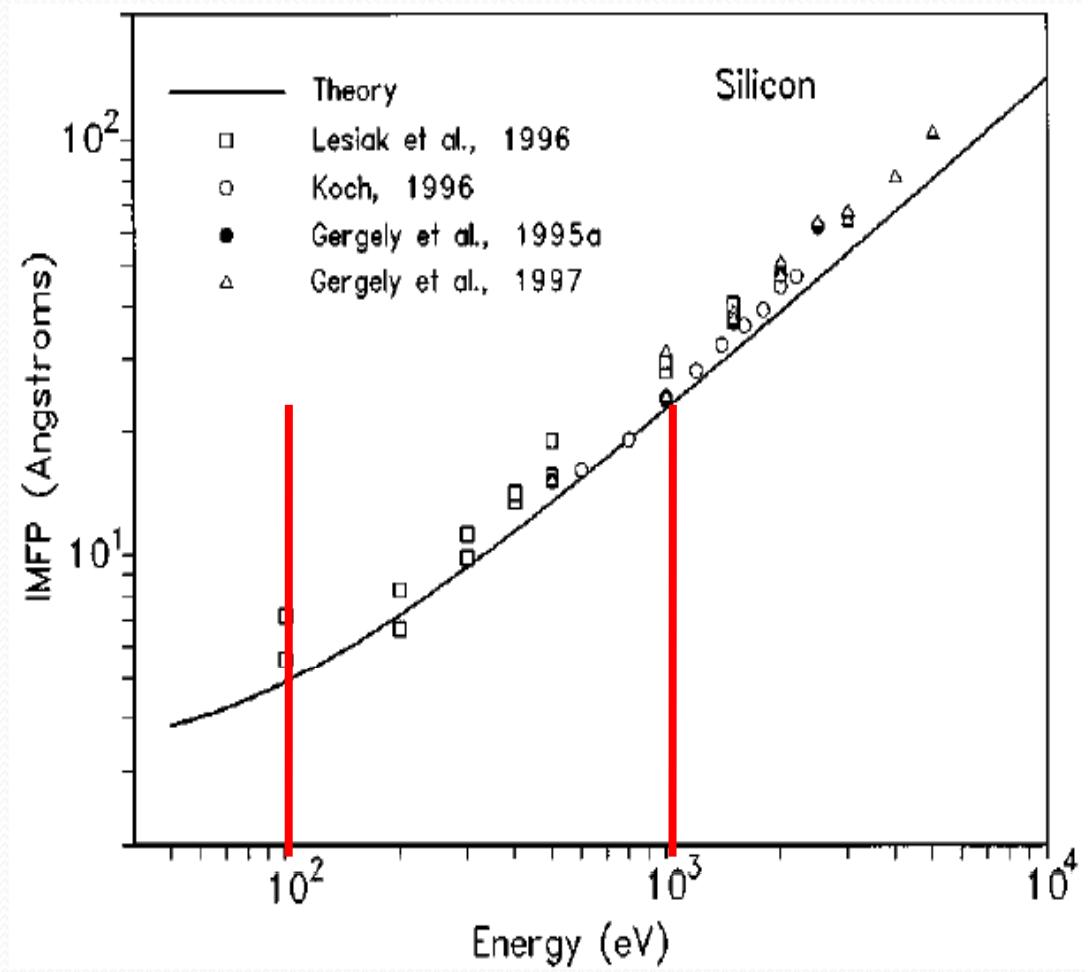
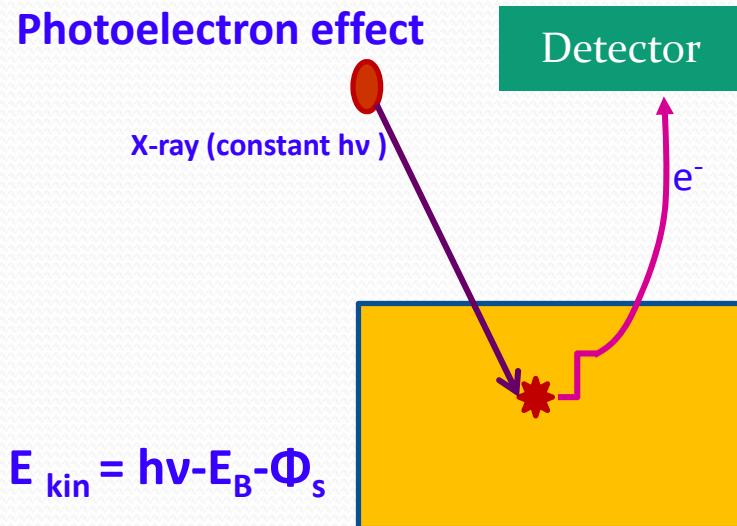
# XPS Cartoon Mechanism



XPS:  $E_B = h\nu - E_{kin} - \Phi_s$  For example,  $E_B$  for  $S2p_{3/2}$

# Surface Sensitivity

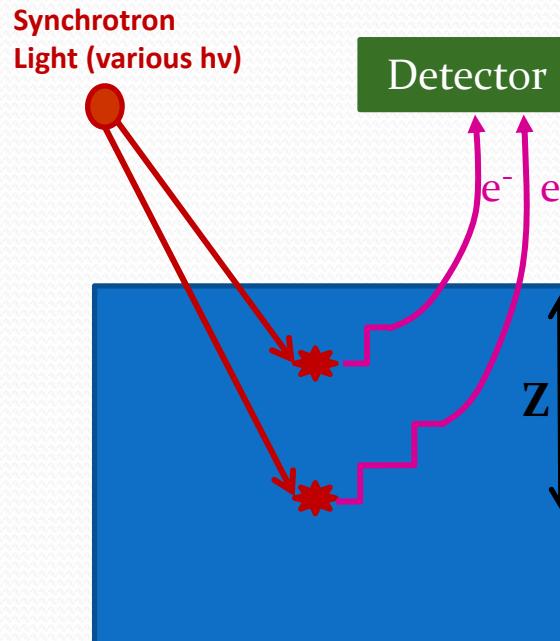
- Electron Inelastic Mean Free Path



# Depth profile experiment and inelastic mean free path (IMFP)

- Continuous
- Changeable

Depth profile experiment



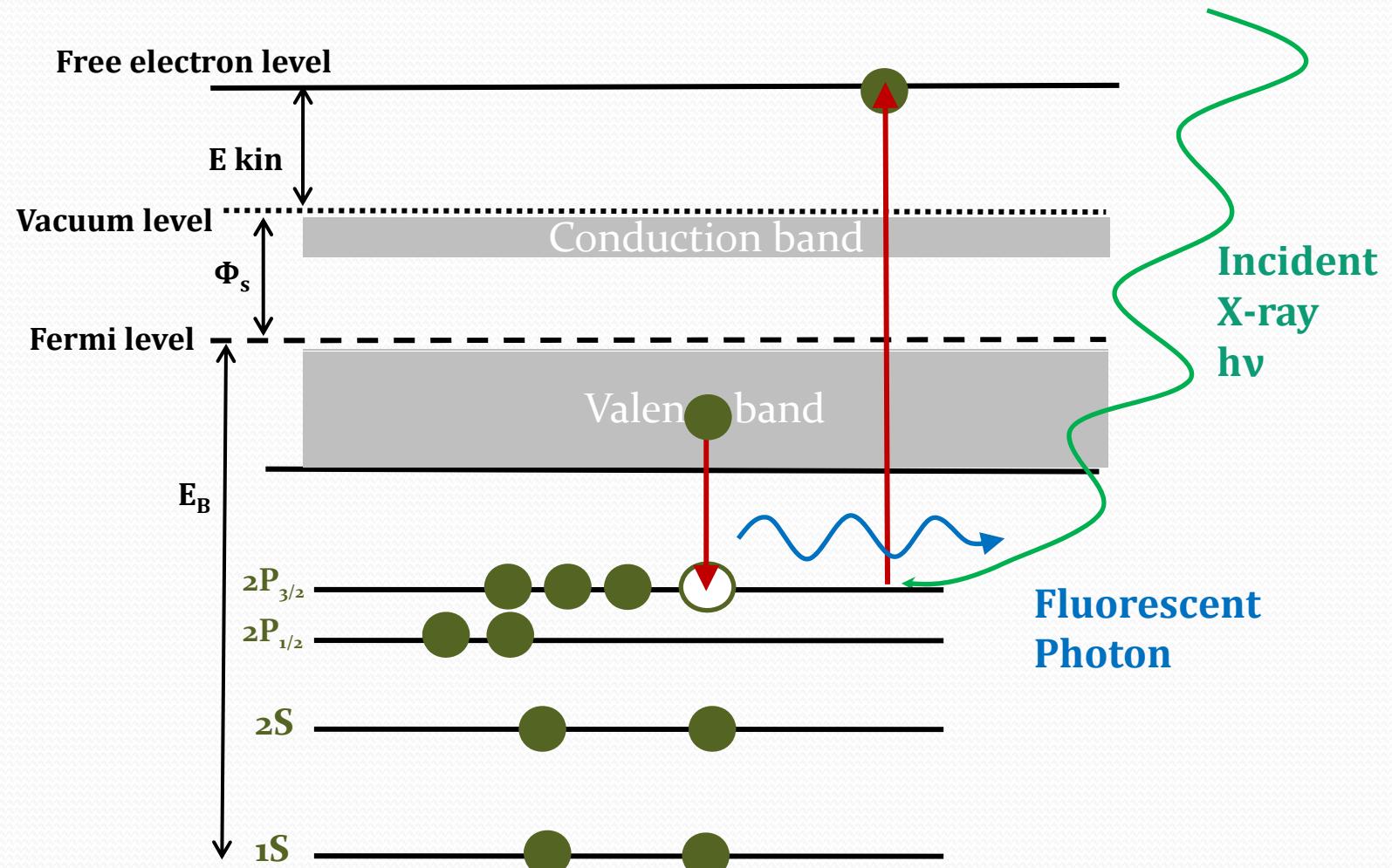
Photoelectrons with different kinetic energies come from different depth of the sample.



# XES and XAS

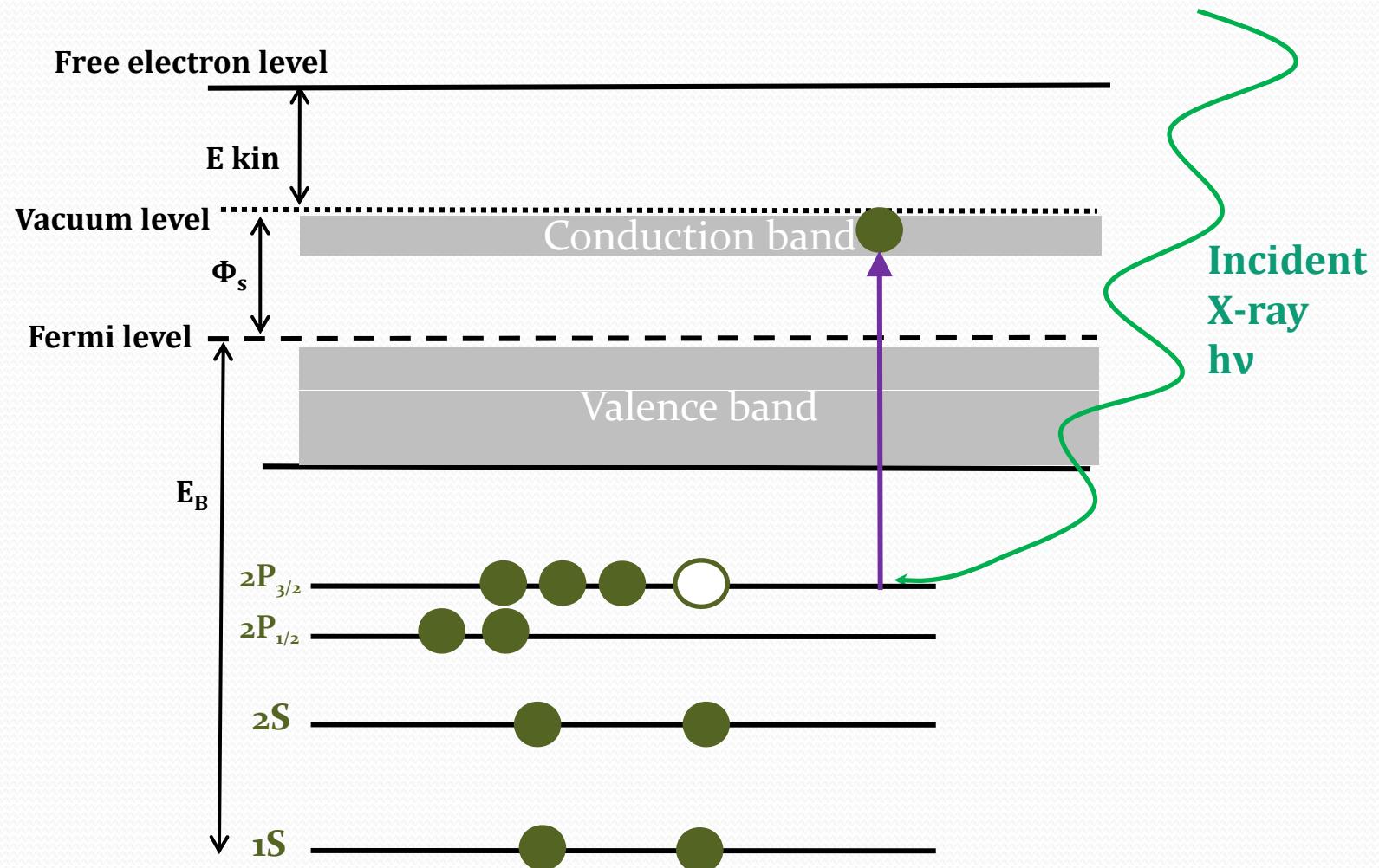
## Two Photons process: Photon in Photon out

# XES Cartoon Mechanism



XES:(Photon in Photon out) Fluorescent photon created by electron decay from valence band to core level

# XAS Cartoon Mechanism



XAS: Electrons from core level to unoccupied conduction band, For example,  $A_1$  for S\_L edge

$$E_A = h\nu - h\nu_T \text{ For example}$$

# Limitation

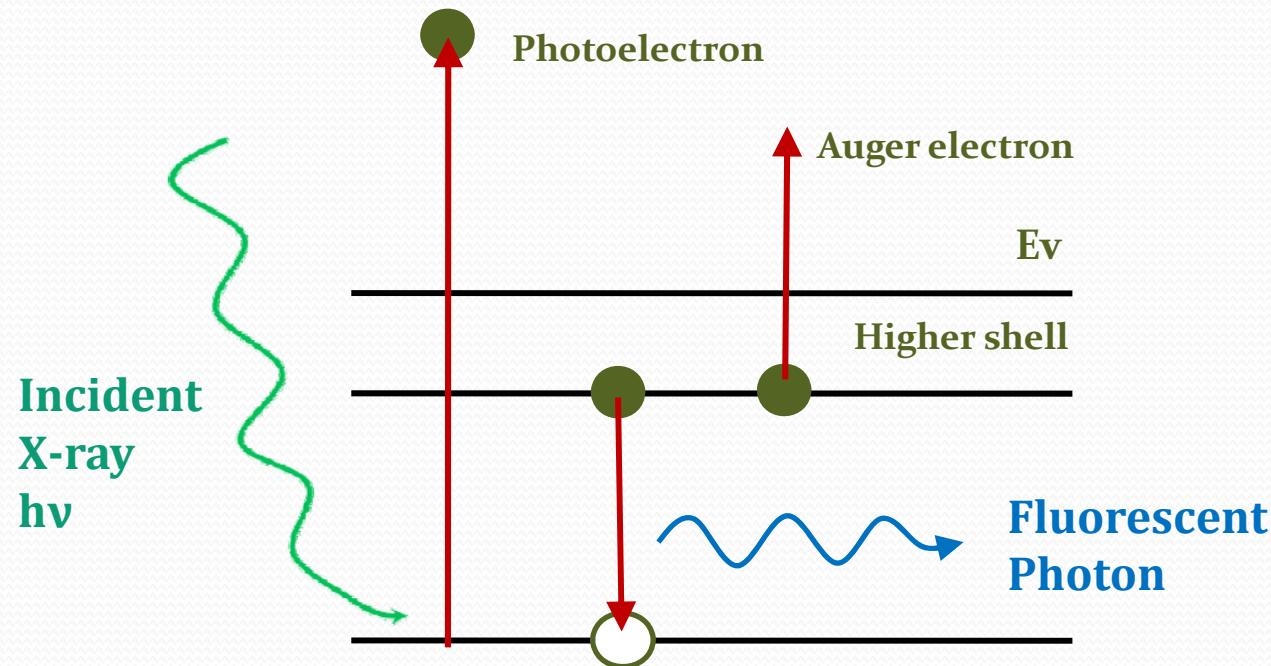
- **Traditional Measurement (Transmission)**

- Signal-to-background ratios limited by thickness ( $\sim 500\text{\AA}$ )
- Radiation damage
- Reflection geometry experiment
- Surface Sensitive?!

- **We can only collect electron not photon in beamline 11.0.2**

# Electron Yield

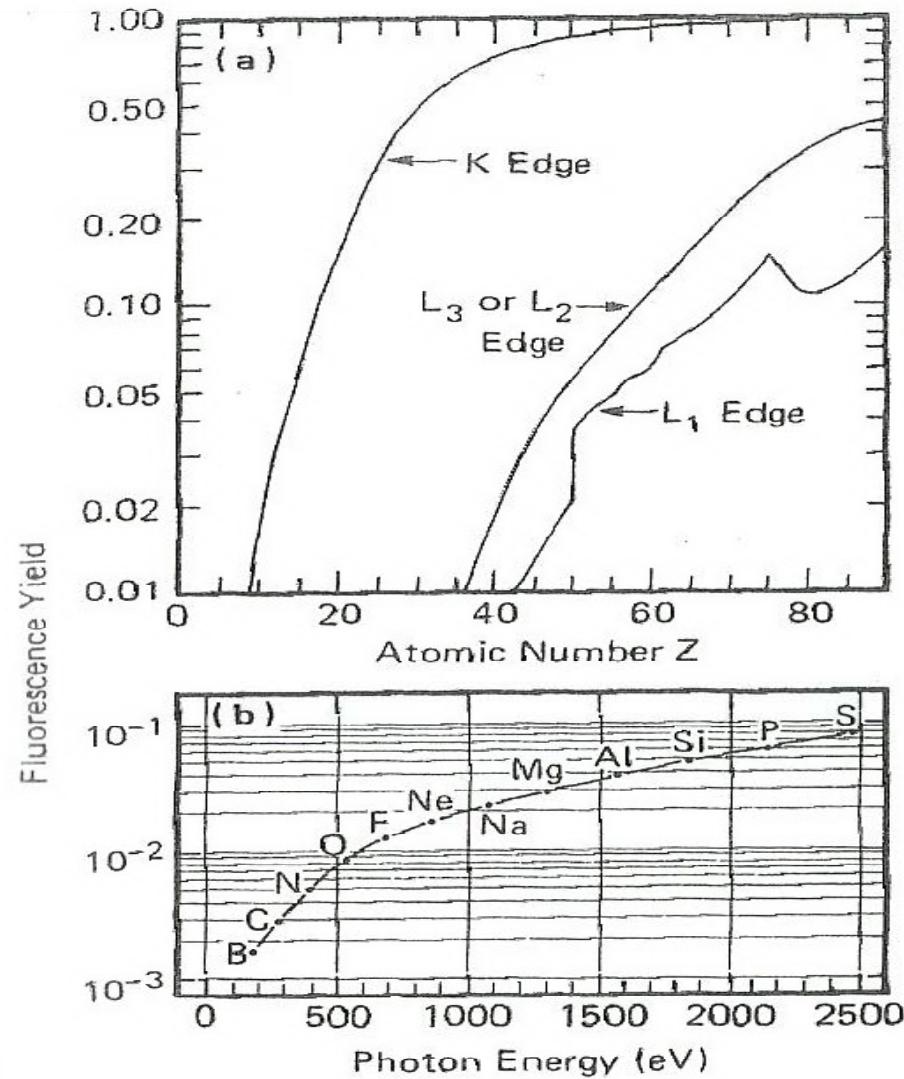
- Electron Yield or Secondary Electron
  - Auger electron & Fluorescent Photon



# Electron Yield

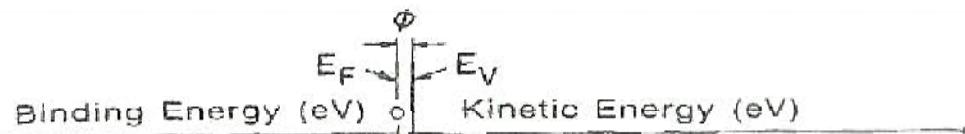
- Auger electron yield dominate

- For K shell excitation of low-Z atoms
- For L shell excitation of all Z < 90
- C, N O, S, Si



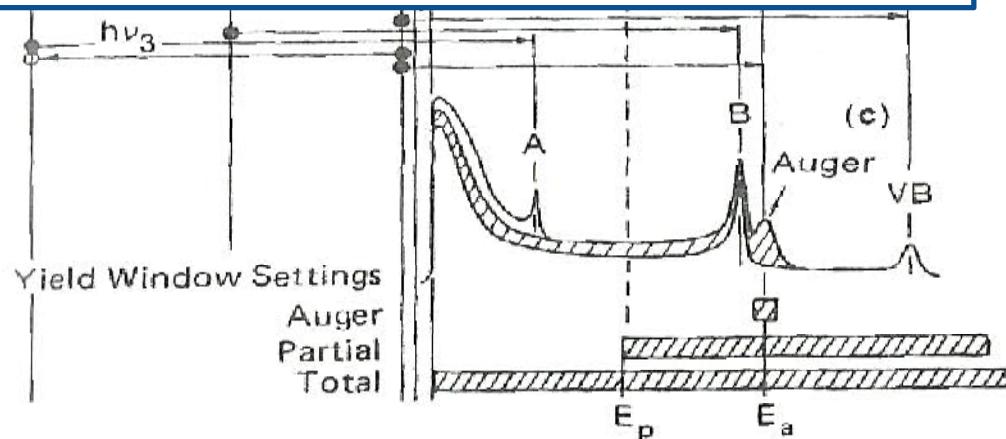
J. Phys. Chem. Ref. Data 8, 307 (1979)

# Electron Yield



- **Detection Mode**

- Auger Electron Yield (AEY)
- Partial Electron Yield (PEY)
- Total Electron Yield (TEY)



Stöhr, Joachim, NEXAFS Spectroscopy, Springer-Verlag 1996



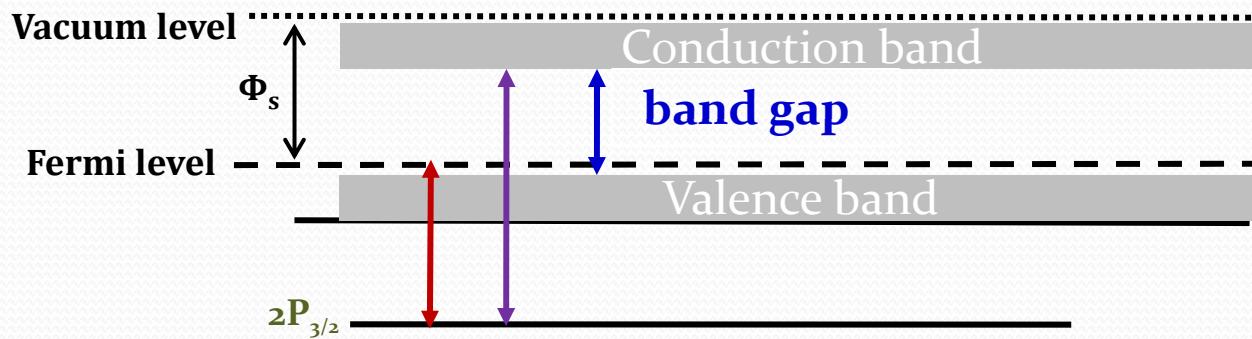
# **Reviews:**

# **XPS & Electron Yield XAS**

# **Band Gap Determination**

# Fermi Surface Determination

- Testing Experiment on Si (band gap 1.11eV)

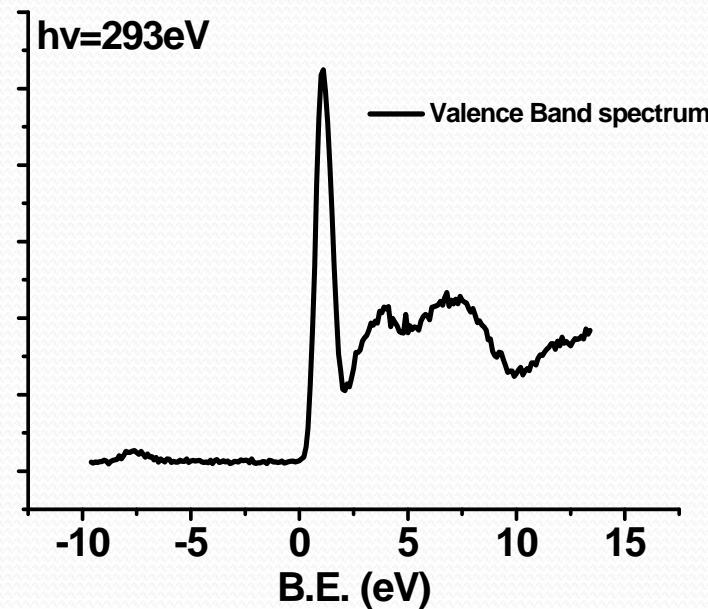


- Binding Energy calibration

- Au  $4f_{7/2} = 84.00$  eV
- Ag  $3d_{5/2} = 368.27$  eV
- Cu  $2p_{3/2} = 932.67$  eV

M. P. Seah, Surf. Interface Anal. 14, 488 (1989)

- Valence Band Spectrum



# Take-home messages

- **Band Gap Determination by XPS+XAS**
  - Fermi Surface Determination by Valence Band Spectrum
  - Fermi Surface Determination by Binding Energy Calibration
  - Testing Experiment on Si
- **Band Gap Determination by Electron Yield XES+XAS**
  - Density of State Information of Valence band and Conduction band
  - Core Hole Effect Analysis